



# 60V N-CHANNEL SELF PROTECTED ENHANCEMENT MODE INTELLIFET MOSFET WITH PROGRAMMABLE CURRENT LIMIT

#### **Product Summary**

Continuous Drain Source Voltage V<sub>DS</sub> = 60V

On-State Resistance: 500mΩ

Nominal Load Current (V<sub>IN</sub> = 5V): 1.4A

Clamping Energy: 550mJ

#### **Description**

The ZXMS6003G is a self-protected low-side IntelliFET<sup>TM</sup> MOSFET. It features monolithic overtemperature, overcurrent, overvoltage (active clamp), and ESD protected logic level functionality. It is intended as a general purpose switch with status indication and programmable current limit.

#### **Applications**

- Especially Suited for Loads with a High In-Rush Current Such as Lamps and Motors
- All Types of Resistive, Inductive, and Capacitive Loads in Switching Applications
- μC Compatible Power Switch for 12V and 24V DC Applications
- Replaces Electromechanical Relays and Discrete Circuits
- Linear Mode Capability The current-limiting protection circuitry
  is designed to deactivate at low V<sub>DS</sub> in order not to compromise
  the load current during normal operation. The design max. DC
  operating current is therefore determined by the thermal
  capability of the package/board combination rather than by the
  protection circuitry.
  - Note: This does not compromise the product's ability to selfprotect during short-circuit load conditions.
- Current Limit is Programmable via an External Resistor R<sub>PROG</sub>
   Connected Between Status and IN pins
- Status Pin Voltage Reflects the Gate Drive Applied Internally to the Power MOSFET
- With  $V_{IN} = 5V$  and  $R_{PROG} = 24k\Omega$ :
  - Status Voltage: 5V Indicates Normal Operation
  - Status Voltage: 2V to 3V Indicates the Device is in Current-Limiting Mode
  - Status Voltage <1V Indicates the Device is in Thermal Shutdown

#### **Features and Benefits**

- Current Limit Programmable via External Resistor
- Status Pin (Analog Status Indication)
- Logic Level Input
- Short-Circuit Protection with Auto Restart
- Overvoltage Protection (Active Clamp)
- Thermal Shutdown with Auto Restart
- Overcurrent Protection
- Input Protection (ESD)
- Load Dump Protection (Actively Protects Load)
- High Continuous Current Rating
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

#### **Mechanical Data**

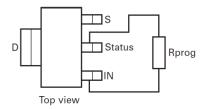
- Case: SOT223 (Type DN)
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish (3)
- Weight: 0.112 grams (Approximate)

SOT223 (Type DN)



Top View

Note:  $R_{\mbox{\scriptsize PROG}}$  must be connected between the Status and IN pins.



Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

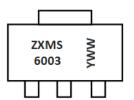


#### **Ordering Information** (Note 4)

Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
ZXMS6003GTA	ZXMS6003	7	12	1000 Units

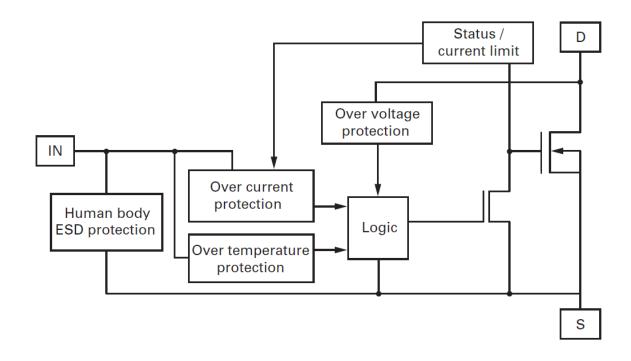
Note: 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

### **Marking Information**



 $\begin{array}{lll} ZXMS6003 = Product \ Type \ Marking \ Code \\ YWW = Date \ Code \ Marking \\ Y \ or \ \overline{Y} = Last \ Digit \ of \ Year \ (ex: 8 = 2018) \\ WW \ or \ \overline{W}W = Week \ Code \ (01 \ to \ 53) \\ \end{array}$ 

### **Functional Block Diagram**





### **Absolute Maximum Ratings** ( $@T_A = +25^{\circ}C$ , unless otherwise stated.)

Parameter	Symbol	Limit	Unit
Continuous Drain-Source Voltage	$V_{DS}$	60	V
Drain-Source Voltage for Short-Circuit Protection V <sub>IN</sub> = 5V (Note 5)	V <sub>DS(SC)</sub>	36	V
Drain-Source Voltage for Short-Circuit Protection V <sub>IN</sub> = 10V (Note 5)	V <sub>DS(SC)</sub>	20	V
Continuous Input Voltage	V <sub>IN</sub>	-0.2 to +10	V
Peak Input Voltage	V <sub>IN</sub>	-0.2 to +20	V
Operating Temperature Range	$T_J$	-40 to +150	°C
Storage Temperature Range	T <sub>STG</sub>	-55 to +150	°C
Power Dissipation at @T <sub>A</sub> = +25°C (Note 6)	$P_{D}$	2.5	W
Continuous Drain Current @V <sub>IN</sub> = 10V; T <sub>A</sub> = +25°C (Note 6)	I <sub>D</sub>	1.6	Α
Continuous Drain Current @V <sub>IN</sub> = 5V; T <sub>A</sub> = +25°C (Note 6)	I <sub>D</sub>	1.4	Α
Continuous Source Current (Body Diode) (Note 6)	Is	3	Α
Pulsed Source Current (Body Diode) (Note 7)	Is	8	Α
Unclamped Single Pulse Inductive Energy	E <sub>AS</sub>	550	mJ
Load Dump Protection	VLOADDUMP	80	V
Electrostatic Discharge (Human Body Model)	V <sub>ESD</sub>	4000	V
DIN Humidity Category, DIN 40 040	_	E	_
IEC Climatic Category, DIN IEC 68-1	_	40/150/56	_

### Thermal Resistance (@T<sub>A</sub> = +25°C, unless otherwise stated.)

Parameter	Symbol	Value	Unit
Junction to Ambient (Note 6)	R <sub>ÐJA</sub>	50	°C/W
Junction to Ambient (Note 7)	R <sub>ÐJA</sub>	28	°C/W

Notes:

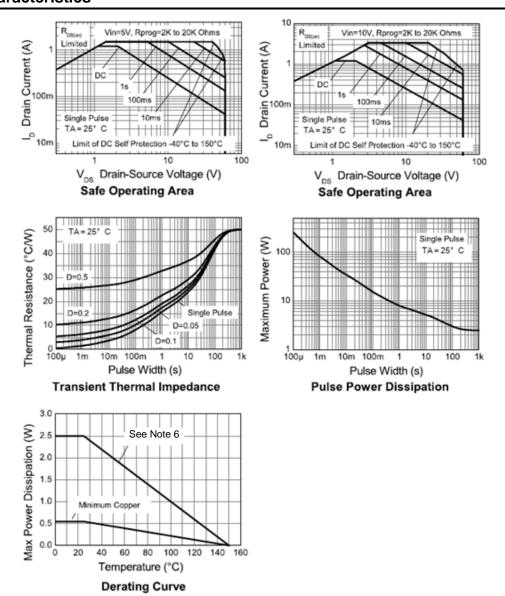
<sup>5.</sup> For  $I_{D(LIM)}$  < 1.2A (see safe operating area curve).

<sup>6.</sup> For a device surface mounted on 50mm × 50mm × 1.6mm FR-4 board with a high coverage of single sided 2oz weight copper.

<sup>7.</sup> For a device surface mounted on FR-4 board and measured at t < 10s.



### **Thermal Characteristics**





### **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise stated.)

Parameter	Symbol	Min	Тур	Max	Unit	Conditions	
Static Characteristics							
Drain-Source Clamp Voltage	V <sub>DS(AZ)</sub>	60	70	75	V	I <sub>D</sub> = 10mA	
Off State Drain Current	I <sub>DSS</sub>	_	0.1	3	μΑ	V <sub>DS</sub> = 12V, V <sub>IN</sub> = 0V	
Off State Drain Current	I <sub>DSS</sub>	_	3	15	μΑ	V <sub>DS</sub> = 32V, V <sub>IN</sub> = 0V	
Input Threshold Voltage (Note 8)	V <sub>IN(TH)</sub>	1	2.1	_	V	$V_{DS} = V_{GS}$ , $I_D = 1mA$	
Input Current	I <sub>IN</sub>	_	0.7	1.2	mA	V <sub>IN</sub> = 5V	
Input Current	I <sub>IN</sub>		1.5	2.7	mA	V <sub>IN</sub> = 7V	
Input Current	I <sub>IN</sub>	_	4	7	mA	V <sub>IN</sub> = 10V	
Static Drain-Source On-State Resistance	R <sub>DS(ON)</sub>		520	675	mΩ	V <sub>IN</sub> = 5V, I <sub>D</sub> = 0.2A	
Static Drain-Source On-State Resistance	R <sub>DS(ON)</sub>		385	500	mΩ	V <sub>IN</sub> = 10V, I <sub>D</sub> = 0.5A	
Current Limit (Note 9)	I <sub>D(LIM)</sub>	0.2	0.3	0.4	Α	$V_{IN} = 5V$ , $V_{DS} = 10V$ , $R_{PROG} = 20k$	
Current Limit (Note 9)	I <sub>D(LIM)</sub>	0.7	0.9	1.2	Α	V <sub>IN</sub> = 10V, V <sub>DS</sub> = 10V, R <sub>PROG</sub> = 20k	
Dynamic Characteristics							
Turn-On Time (V <sub>IN</sub> to 90% I <sub>D</sub> )	ton	_	3	_	μs	$R_{PROG}$ = 20k, $R_L$ = 22 $\Omega$ , $V_{IN}$ = 0 to 10V, $V_{DD}$ = 12V	
Turn-Off Time (V <sub>IN</sub> to 90% I <sub>D</sub> )	toff	_	13	_	μs	$R_{PROG} = 20k$ , $R_L = 22\Omega$ , $V_{IN} = 10V$ to $0V$ , $V_{DD} = 12V$	
Slew Rate On (70 to 50% V <sub>DD</sub> )	dV <sub>DS</sub> /dt <sub>ON</sub>	_	8	_	V/µs	$R_{PROG}$ = 20k, $R_{L}$ = 22 $\Omega$ , $V_{IN}$ = 0 to 10V, $V_{DD}$ = 12V	
Slew Rate Off (50 to 70% V <sub>DD</sub> )	dV <sub>DS</sub> /dt <sub>ON</sub>	_	3.2	_	V/µs	$R_{PROG}$ = 20k, $R_L$ = 22 $\Omega$ , $V_{IN}$ = 10V to 0V, $V_{DD}$ = 12V	
Protection Functions (Note 10)		l .	u.	I.			
Required Input Voltage for Over- Temperature Protection	V <sub>PROT</sub>	4.5	_	_	V	_	
Thermal Overload Trip Temperature	T <sub>JT</sub>	+150	+175	_	°C	_	
Thermal Hysteresis	_		+1	_	°C	_	
Unclamped Single Pulse Inductive Energy T <sub>J</sub> = +25°C	E <sub>AS</sub>	550	_	_	mJ	$I_{D(ISO)} = 0.7A, V_{DD} = 32V$	
Unclamped Single Pulse Inductive Energy T <sub>J</sub> = +150°C	E <sub>AS</sub>	200	_	_	mJ	$I_{D(ISO)} = 0.7A, V_{DD} = 32V$	
Status Flag							
Normal Operation	VSTATUS	_	4.95	_	V	V <sub>IN</sub> = 5V	
Current Limit Operating	V <sub>STATUS</sub>		2.5		V	$V_{IN} = 5V$	
Thermal Shutdown Activated	V <sub>STATUS</sub>		0.2	1	V	V <sub>IN</sub> = 5V	
Normal Operation	V <sub>STATUS</sub>	_	8	_	V	V <sub>IN</sub> = 10V	
Current Limit Operation	V <sub>STATUS</sub>	_	3	_	V	V <sub>IN</sub> = 10V	
Thermal Shutdown Activated	V <sub>STATUS</sub>	_	0.35	1	V	V <sub>IN</sub> = 10V	
Inverse Diode							
Source Drain Voltage	V <sub>SD</sub>	_	_	1	V	$V_{IN} = 0V, -I_D = 1.4A$	

Notes:

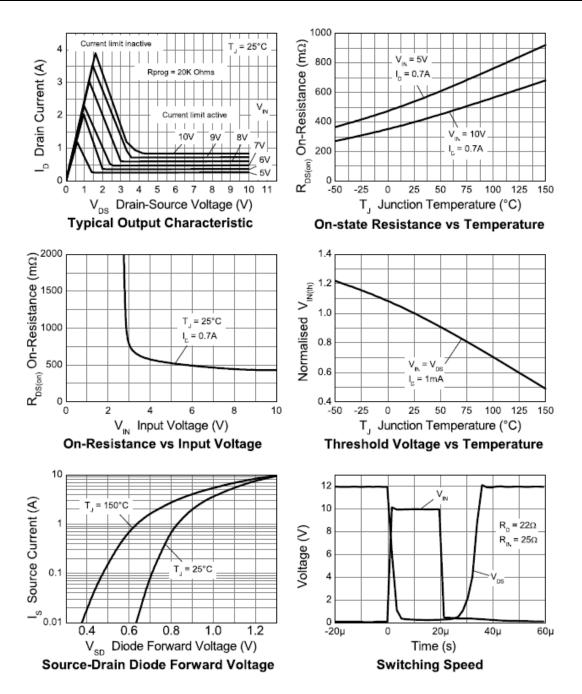
<sup>8.</sup> Protection features may operate outside spec for  $V_{\text{IN}}$  < 4.5V.

<sup>9.</sup> The drain current is limited to a reduced value when  $V_{DS}$  exceeds a safe level.

<sup>10.</sup> Integrated protection functions are designed to prevent IC destruction under fault conditions described in the datasheet. Fault conditions are considered as "outside" normal operating range. Protection functions are not designed for continuous, repetitive operation.



### **Typical Characteristics**





### **Typical Characteristics (cont.)**

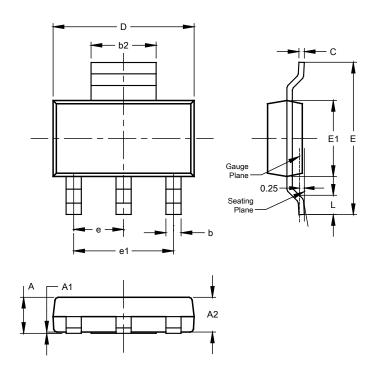
#### **Current Limiting and Over Temp Shutdown Current Limiting and Over Temp Shutdown** Status Indication at Vin=5V Status Indication at Vin=10V V<sub>IN</sub> =5V Normal Operation Typical VStatus (V) Typical VStatus (V) Rprog=24kΩ Rprog=24kΩ Over Temp Over Temp Shutdown Shutdown 75 100 125 150 175 200 225 250 Typical Temperature (°C) 75 100 125 150 175 200 225 250 Typical Temperature (°C) V<sub>IN</sub> =10V V<sub>IN</sub> =5V Typical VStatus (V) Typical VStatus (V) Normal Operation Normal Operation Current limit operating Current limit operating 20 60 60 40 20 100 Rprog $(k\Omega)$ Rprog $(k\Omega)$ VStatus vs Rprog @ Vin=10V VStatus vs Rprog @ Vin=5V Normal Operation Typical VStatus (V) Current Limit (A) Rprog=24kΩ V<sub>IN</sub> = 10V T, = 25°C 0.1 Current limit operating 2 L 5 40 60 Rprog (kΩ) ō 20 100 7 Vin (V) **Current Limit vs Rprog** VStatus vs Vin



#### **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT223 (Type DN)

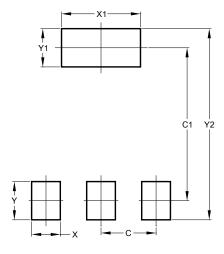


SOT223 (Type DN)				
Dim	Min	Max	Тур	
Α		1.70		
A1	0.01	0.15		
A2	1.50	1.68	1.60	
b	0.60	0.80	0.70	
b2	2.90	3.10		
С	0.20	0.32		
D	6.30	6.70		
Е	6.70	7.30		
E1	3.30	3.70		
е			2.30	
e1			4.60	
L	0.85			
All Dimensions in mm				

### **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### SOT223 (Type DN)



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Υ	1.60
Y1	1.60
Y2	8.00



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